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Wednesday → 8/26/2015
→ first class

5

Friday → 8/28/2015
→ Safety

Wednesday

8/26/2015

- Lab safety basis online (NDNF)
↳ Send to Prof. by Monday
- NDNF Safety Overview (completed Fr. 8/26/2015)
- NDNF Safety Manual
.adv/mduf/safety/index.htm / (Email to Prof.)

Don't EVER BE LATE!!!

Office hours
Fr.: 3-4p
M,W: 3-4p

Cesar: T 11-12 (S,R. B20)

Sandhya: Th 1-2 (SR 228)

Book: Microchip Manufacturing

Sakai: Course Website

Monday Aug. 31, 2015

New Group 5

↳ Training certificate & Agreement

Submitted 8/31/2015

Jin chi (Jin-chu^{re})

Bases are worse burns than acids

Basic = Caustic

Solvents \Rightarrow stainless steel tools

HMDs (Solvent in wrong hood)

Don't Put Metal in an oxidation Furnace!

Marie \rightarrow Stanford "Silicon Run I" (2nd ed.)

Ruth A. Carriz...?

Wednesday Sept. 2, 2015

□ get book! (or access to it)

Make appointments (Snyder, Sandhya, Cesar)

1. Have water ready to push stepper
(check focus)

2. " " (check alignment)

START Practice lab ASAP; finish by
early next week!

See cleanroom Notebook Guidelines

→ Create A picture Notebook (date each page)

↳ Do it as you go! Submit in PDF

→ each person should write into notebook → add initials



Lab Procedure is up online!

↳ and in cleanroom!

(Etch vs develop?)

→ Write "Guidelines"

↳ must read Procedure at least

train & understand before lab work.

↳ Cancelling or adjusting
schedule must happen > 24 hrs.
before lab work.



Research Writing! (Most important)

1. When to stop!

2. What do leave out

(just as important as what
is put in!)



It is a mathematical fact that
only two layers (of metal) are required
to build any circuit.



The best technology can perform is just
before it is about to be replaced

All calculations dissipate energy
(counting on fingers, thinking, etc.)

Information is physical!

Manipulating information requires energy

Abacus → Pascalene → Babbage diff.
3000 BC 1642 engine 1832

Video: Babbage's Difference engine No. 2 //
(WIRED)

Elec. Engineers work with electrons
(small & light) →

Konrad Zuse \rightarrow Binary Digital Computer
^{first}
(German, during WWII, so winners never heard of him)

ENIAC (vacuum tubes instead of relays)
 \hookrightarrow 174 kW 17,500 Tubes
5,000 additions/sec.

Energy required to calculate trajectory
" " = to fire a projectile

Bug actually found (in relay!)

Bill Scherckley \rightarrow Nobel Prize Winner
Sperm Bank contributor
 \hookrightarrow Started silicon valley b/c no-one wanted
to work with him

Friday Sept. 4, 2015

- 446 : Training Wednesday Tuesday
- Finish practice lab by Thursday

RJE \Rightarrow Greg's Baby

"Marketing people lie... get you to buy things you don't want, to impress people you don't like..."

↳ Dr. Greg

Small is good, but cheap is better

1935: 1 logic gate/hr.
2015: 10¹⁰ " "/hr.

} Productivity
is key

Core i7 $\rightarrow 8 \times 10^{10}$ parts/in³

Moore's law \rightarrow "license to print money"

↳ exponentially more productivity

"Women are more patient than men

you make a guy do this, and

he's gonna kill somebody..."

→ Dr. Greg

#gradschool

"They got to the moon with 8K bits.."
↳ Dr. Greg

More than 2K transistors on the chip were
going to make

logic dissipates more energy
than cache memory

Facebook → server farm in Norway
↳ sell waste heat!!!

Energy dissipation issue addressed

by moving to many-cores, around
year 2,000

↳ Amdel's Law

↳ saturation of performance
@ high core #.

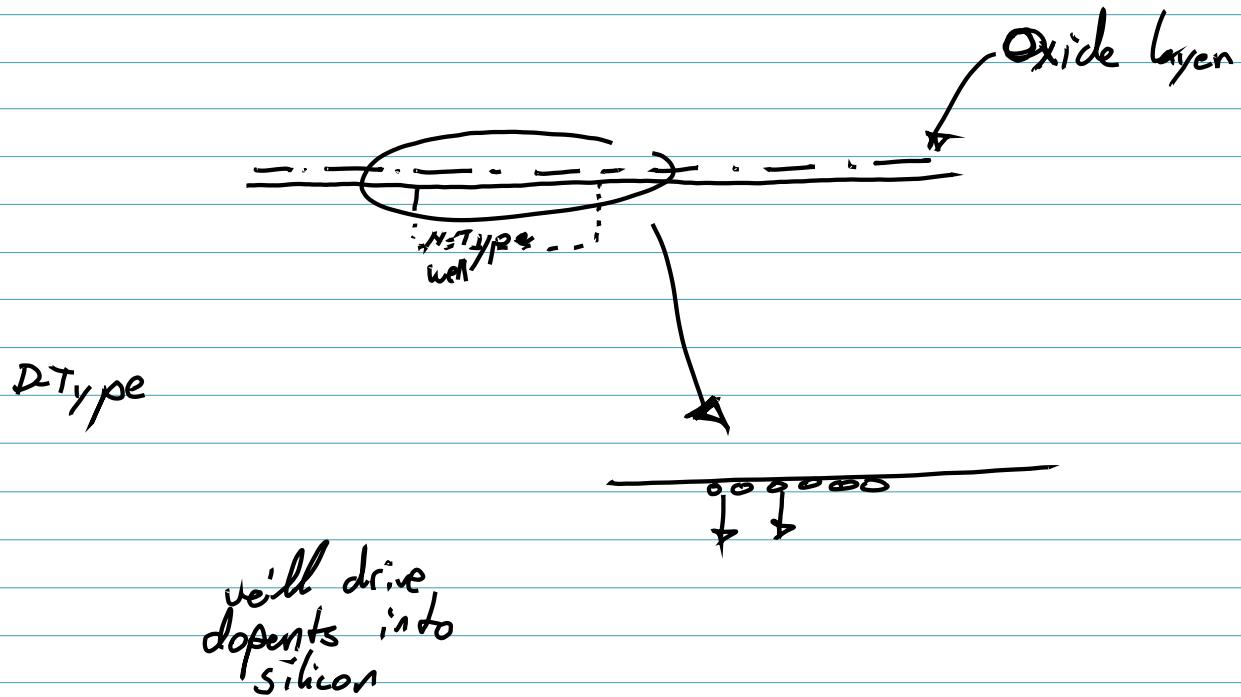
Apple switched from IBM to Intel to
reduce heat exchanger size

How much is 300nm under north? (~50% yield)

"My wife is Italian, and she has scary
cousins which will make you
disappear for much less [time] than that..."
↳ Dr. Greg

END OF HISTORY

CMOS Process Flow:



Step 1: 1000 Å deep notch into Silicon

Layer 0 → □

(will make 1200 sand chips)

You can program your own song

64 notes // → Excel file

0.75 μ sign oscillator (goal is to make work)

Monday Sept. 7, 2005

□ Finish Practice lab by Thursday

4/6: 3p Tuesday

~~Wednesday~~

~~an electrical assembly~~

□ Tell group-mates to get remote control

□ Skim Ch. 2 - 4

→ We'll probably

work on Wednesday

Half of the world's transistors were made in the last
3-4 years.

No one → double
transistors
or chip



Sand → SiO₂ → ... → Water

Quartzite

Carbon payback on Silicon Solar cells ~ 3 yrs.

MGS → Metal Grade Silicon

EGS → Electronic Grade Silicon

BAD

- Kilo-gram: 1. its gaining weight (we think)
- Physical object 2. Not attainable from scratch somewhere else
3. It's in France

Bechtel → big thing of single crystal Silicon
Barle

What is an internal diameter blade?

(FMS) Surface Roughness of our wafers;
about 1 nm.

A

Wednesday Sept. 9

S. Wolf → Microchip Manufacturing

Skim Chapters 2-4 & Ch. 13

Start "real" notes tomorrow (Thursday, Sept. 10)

"Best way to get sand from Intel is to touch a wafer with tweezers."

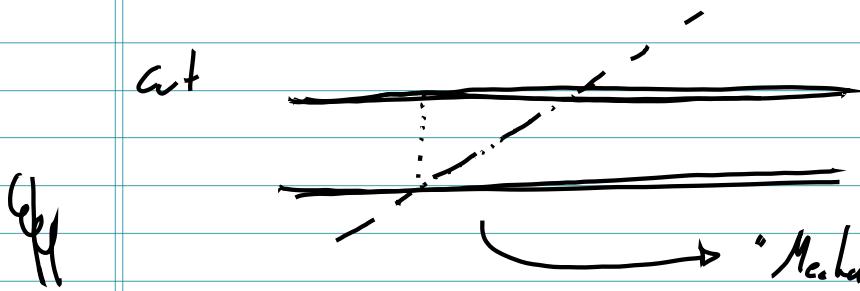
↳ [Intel wafer manufacturing is completely automated.]

Q1: What is the "end of scaling?"

300mm wafers are 2mm thick

Oxidation:

"Silicon oxide is God's gift to humanity!"



• Mechanically amorphous distance
to examine profile"

[cut on an angle instead of perpendicular]

Friday Sept. 11.

i. Take wafers out of SPD and they go directly into the furnace

446: Goal: N-well done by next Friday

"Professors are all sadistic bastards..."
↳ Dr. Greg

1. Alignment & etch
2. First oxidation ^{use} (no later than 8:30a)
3. Spin. N-well Litho! (Tuesday morning)

(Photo-notebook → PDF → Sukai (two weeks))

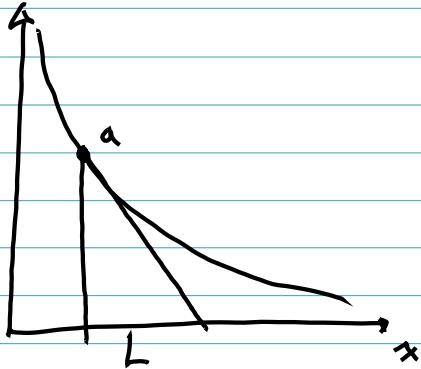
Things that happen with RT means
there is probably diffusion happening

Oxidation is a thermally activated process.

$$D = D_0 \exp\left(-\frac{E_A}{kT}\right)$$

Arrhenius
Relationships

'I call the exponential function
the Sarah Palin/Twerp equation, because
no matter what you do, it never goes away.'
↳ Dr. Greg



where 'a' is a point, the line is a tangent,
and 'L' is the characteristic length

$$e^3 = 20$$

"If you put a man and a
woman in a room @ opposite walls, when
will they meet?"

mathematician → never
engineer → they'll get close enough

& they cover half the
distance between
them each instant

SiO_2 density is essentially the same
(oxide layer) (except right @ interface)

Hydrogen diffuses very easily (some hydrogen cars are
difficult to produce)

"You are a walking bag of sodium." Up Pr. 6

You can't get sodium off a wafer
↳ Picture of threshold in color
preserved hand-print

Wolf is wrong on pg. 219

Oxide loves water!!!

SiO_2 is hydrophilic.

Wet Oxide \rightarrow thicker

Dry Oxide \rightarrow Better surface Quality

So, typically Dry \rightarrow wet \rightarrow Dry

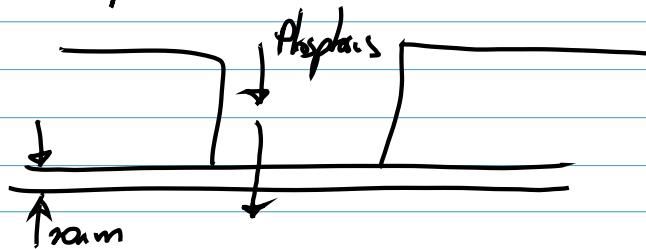
Monday Sept. 14. 2015

Goal: N-well done by Friday

Be Ready by 8:30a Friday)

will grow ~20nm oxidation layer

ion implantation



Dry Oxidation is slightly more dense (than wet)

Let's say: we do the following oxidation procedure

Pattern $\xrightarrow{\text{Dry} \rightarrow 2 \text{ hr.}}$
 $\xrightarrow{\text{Wet} \rightarrow 2 \text{ hr.}}$

for first step $t=0$, (initial oxide is negligible)

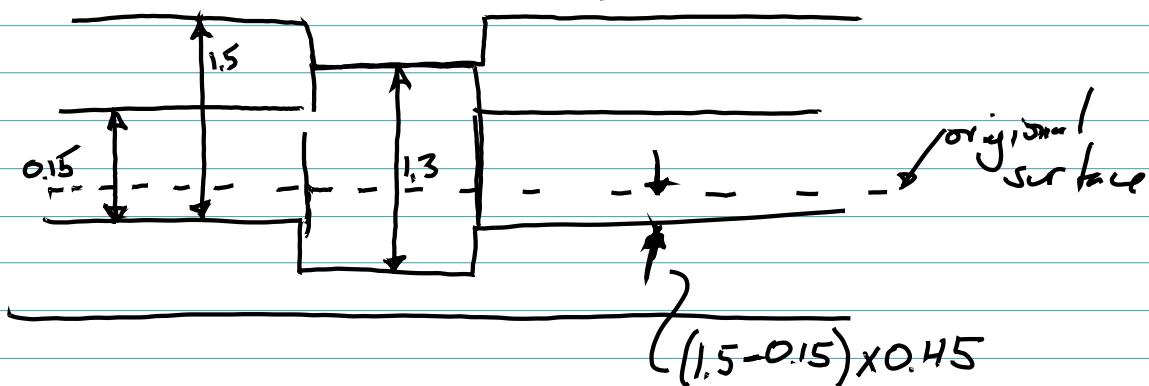
after first oxidation $\frac{0.15}{\text{Pattern}} \xrightarrow{T_0}$

So we have $\frac{0.15}{\text{Pattern}}$ for step 2.

$x_i \rightarrow$ layer thickness

which will yield the new oxide layers
 x_{o_1} and x_{o_2} ,

So, it will look something like



Last Question: Given a desired step height, design the process to accomplish it

XX

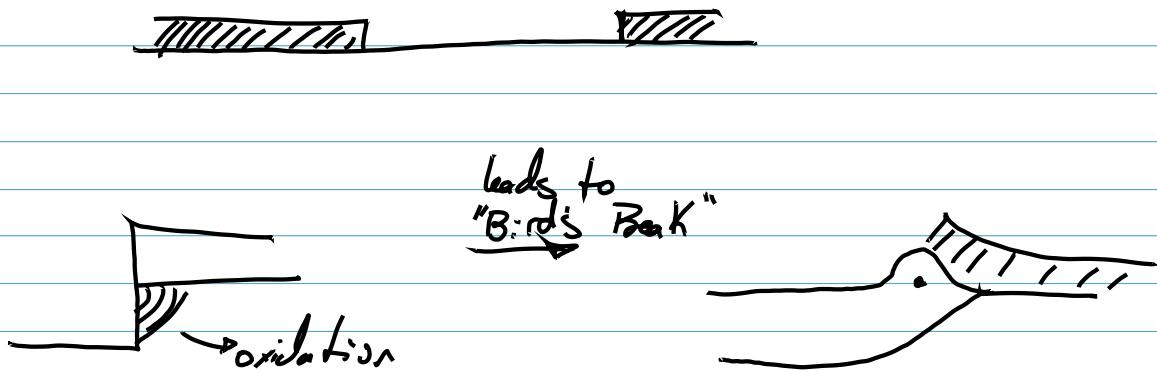
Be careful when using oxide as a diffusion mask, finding using graphs to check minimum thickness

Wednesday Sept. 16, 2015

Patterning Oxide: grow it, then etch it

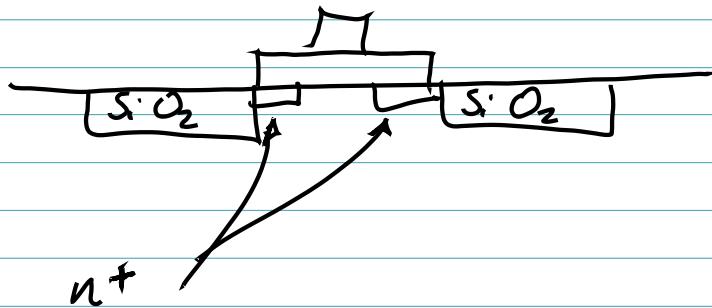
OR Oxidize only where you want it

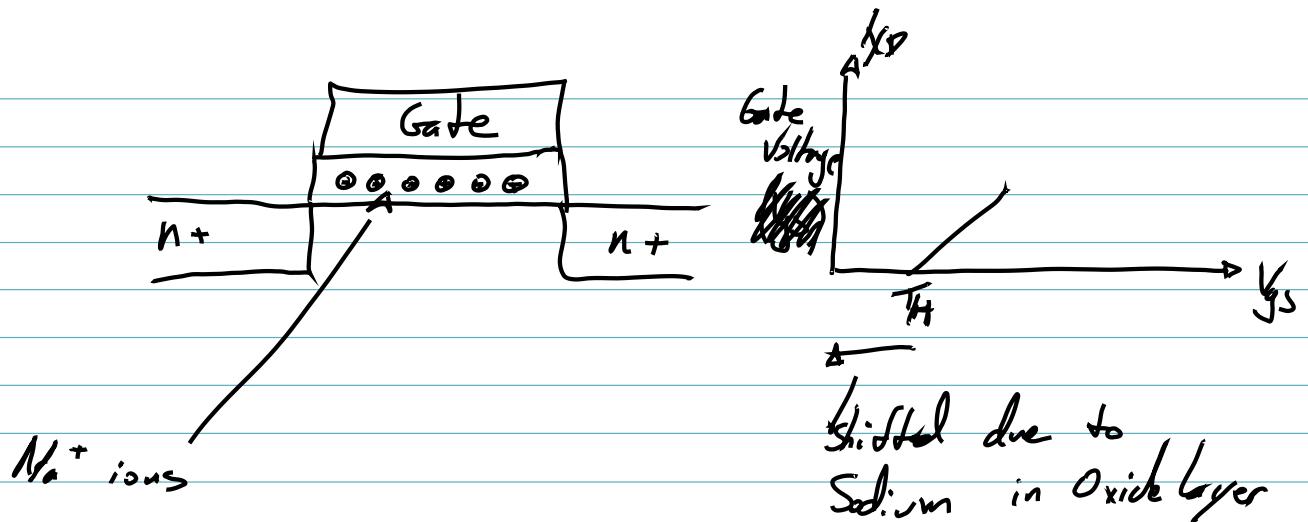
$\text{Si}_3\text{N}_4 \rightarrow$ is really Si_xN_x



∴ Locos has been replaced by shallow trench isolation

So we want:





So, not only will the threshold shift, but it will change due to changing location of ions

trans LC (chlorine containing solvent)
dichloro ethane

TCE (tri-chloro ethylene)
great solvent, but carcinogenic

"Indiana is the upper-peninsula of Alabama")

"Indiana tries to be as backward as it can in lots of ways."

Dr. Greg

Sodium very easily gives up an electron, but then doesn't want to bond to anything near by.

Photolithography

Reading Ch. 18-20

Piranha ($H_2SO_4 : H_2O_2$) (3:1)

Friday Sept. 18. 2015

- Submit photo lab notebook Sakai.
- Lab notebooks will be collected
- Upload Text Problems

"I'm mean for a Reason..." Dr. Greg

Lies My Teacher told Me

You can catch SiO_2

ME wingshields
EE: EC Fab

[Play: Two Perspectives on a Water

light reflects anywhere two different indices of refraction meet

"Spin-casting"

↳ This is how glass was made ☺
thickest at edges

↳ which you would naturally put at the bottom (stronger)

☺ Glass will flow, but over really long time periods

Thickness

$$t \approx \frac{ks^2}{N \cdot \mu_m}$$

$k \rightarrow$ Sanitation
coefficients
(ignorance
constant)

"I love the smell of photorest..." → Dr. Greg

$s \rightarrow$ % solids in PR

Name of P.R.

Low what thickness you
get @ 4,000 RPM

RPM → spin speed

controlling thickness is not good with rpm,
varies as the square root

What you want in P.R. → Cheap

Sensitive
High Res.

Tough
Stable

SU8 is essentially
a photo-sensitive
epoxy

Positive PR

Expensive
High Res.
Aqueous Developers
Easy to Remove
Fairly tough

Typical { Negative PR

Chop
Resolution limited by
Scanning
Solvent Developers
Hard to Remove
Very tough

exposed areas develop away

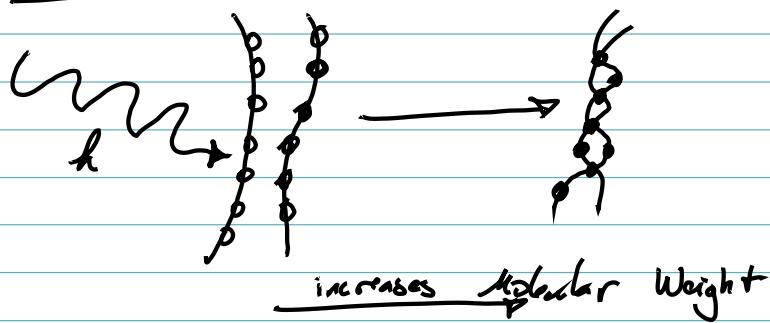
areas exposed
stay

Q1: if you created a square feature with both Pos & Neg., which would be sharper?



(Negative Resist)

Crosslinking:



Dalton (Mass of Carbon-12 atom)

- (Positive Resist) 1. Low molecular weight alkali-soluble resin
2. Photoactive dissolution inhibitor (\$\$)
3. Solvent

(Wolff) Fig. 19-1

Contrast is the most important factor!!!

"If you worked at Intel you could throw your grandmother under a bus to get better contrast."
Dr. Greg

$$\gamma = \frac{1}{\log_2 \left(\frac{D_{\text{exp}}}{D_0} \right)}$$

parallel resist stays } positive resist

All resist gone }

\rightarrow contrast \Rightarrow slope on \rightarrow fraction of resist remaining

\rightarrow exposure dose \rightarrow D_{exp}

Ruby lith \rightarrow

"I got to program in my first programming class or punched cards." \rightarrow Dr. G

Q2: Who is Sam Spade?



Monday Sept 21 2015

"If it doesn't come up, we'll have to call the trolls at OIT." → Dr. G

"Modified Democracy, I ask your opinion, and I do whatever the hell I want..." → Dr. G

You want your layout to require as few flashes as possible.

"That's our workaround for buying carbon plates from those pirates in South Korea." → Dr. G

A Mask is 1-to-1.

A Reticle is used in a reduction system

E-beam is about 2 to 3 nm wide (lithography)

Exposure Methods:

Note: Edge Bead will prevent mask from perfectly contacting PR on wafer.

Note: You can develop edge bead away!!!
Carl Zeiss \approx Lth. 0.35 μm resolution

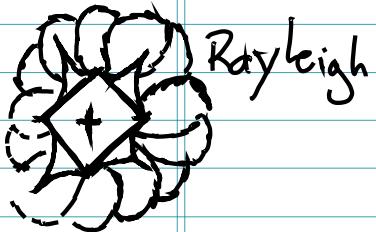
Downside to Contact Lithography is damage to mask and substrate.

◦ Proximity Exposure

↳ however you give up a lot of resolution

◦ Projection Exposure

industry standard, but expensive



$$\sigma = \frac{\lambda k}{NA} \cdot \text{constant}$$

wavelength
constant
 λ
 k
NA
operative

$$= \frac{(0.61) (365 \text{ nm})}{0.4} = 556 \text{ nm} //$$

quoted as 600nm (0.6 μm)

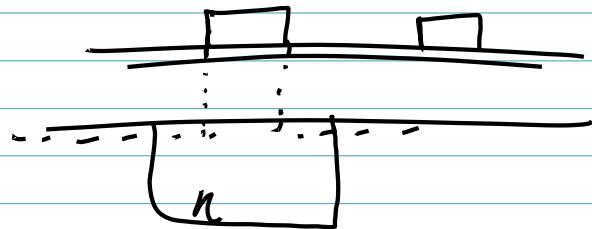
Wednesday Sept 23, 2015

Next Monday Morning in Cleanroom

↳ Active Litho

Si_N_x 100nm

Etch

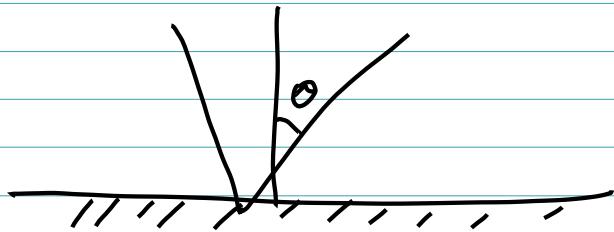


By Next Wednesday!!!

(Tuesday and/or Monday 3-6p)

$$NA = \sin \theta$$

"angle of acceptance"



Modern Stoppers $\sim NA \sim 0.7 - 0.8$

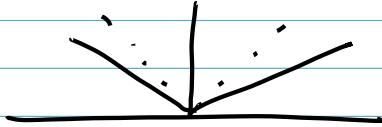
Practical limit 0.9

$$d = \frac{k_2 \lambda}{(NA)^2} \quad k_2 = 0.5$$

'solid angle of light acceptance'

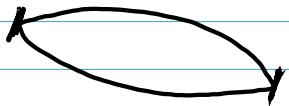
A high NA means lens passes high spatial frequency components \rightarrow leads to high res.

$$0.8 = \sin \theta \text{ Then } \theta = 53^\circ$$



\Rightarrow Big lens

Huge Im refracting lens
 \hookrightarrow become too heavy



lens can only be supported @ edges

But a mirror (reflecting telescope) can be supported from its back.



High NA means large & expensive lens
and small depth of focus.

But for water processing, we want larger depth of focus

for example $d = \frac{0.5 \text{ (365 nm)}}{(0.4)^2}$

depth of focus = 1.1 μm //

Actually: $NA = n \sin \theta$

we want $n > 1$

DI water ≈ 1.3
fluoride ≈ 1.4

(put a fluid between lens & substrate)

"How quickly the transition between
reactions and necessary can happen when
billions of dollars are at stake."

Water does not diffuse through
silicon nitride.

Water/liquids pull particles from the air.

Resolution & ND 5 nm

(using e-beam lithography)

Used by IBM on "custom circuits"

— transistors made 95%, last

metal layer custom directly
written onto top layer of wafer

Friday Sept 25, 2015

446 Use PE-CVD I_{Csinx} 6min.

Nitride Nominal etch time is 3:30.

Active Litho and etch done by next
Wednesday.

Gamma-Rays \rightarrow will kill you

X-Rays \rightarrow " " more slowly

Edward Teller \rightarrow Father of Hydrogen Bomb

To a hammer every problem is a nail,
to Edward Teller every solution is a hydrogen bomb.

Lenses are difficult for X-Rays (they just blast
through everything)
impossible

Really good

\Leftrightarrow if you can make the mask

Intel is not a tech. creator,
it is a tech. exploiter.

IBM however does spend big bucks into
Developing technology.

$$\lambda = 10-14 \text{ nm}$$

Intel & IBM

Extreme Ultra-violet (EUV)

→ a better name are that

"fools the business majors"

No refractive optics @ this wavelength (Ref. index ≈ 1)

Keep in mind reduction (factor of 2) makes
mask easier to fabricate,

Numerical Aperture is the number or order of
waves (light modes?) that can pass through.

Reall \Rightarrow $\sigma = \frac{k_f 1}{NA}$

$k_f \sim 0.6$ (Raleigh refraction)

7:00a Monday!



Monday Sept 28, 2015

"... That's why the Good Lord invented undergarments..."
↳ Dr. Greg

He: Ask yourself what was the best & worst part
of your old job
life
house
city
relationship

?

10 ←
(0.95)
yield had layers

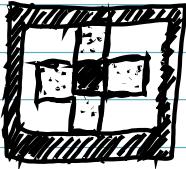
This is why 95% yield is ~~not~~ considered garbage
at Intel

Alignment is Key!!!

Computers can only do two things:

→ add and compare two numbers (which is greater?)

Dr. Snyder's favorite alignment mark



You will typically align your most critical layers to one another.

Contact Lithography → Alignment Marks are simply religious convictions

Veneer

New Homework on Wednesday!

Epitaxial Growth:

446; Read Ch. 17

↳ Substrate used as template to grow more single-crystal material

In epitaxy (homoepitaxy), we grow the same material on top.